Mikhail Sobolev

List of Publications by Year
in descending order

58 papers	365 citations	932766 10 h-index	887659 17 g-index
58 all docs	58 docs citations	58 times ranked	253 citing authors

#	Article	IF	Citations
1	Nonradiative recombination dynamics in InGaN/GaN LED defect system. Superlattices and Microstructures, 2009, 45, 301-307.	1.4	38
2	Deep-level transient spectroscopy in InAs/GaAs laser structures with vertically coupled quantum dots. Semiconductors, 1997, 31, 1074-1079.	0.2	30
3	Generation of the EL2 defect in n-GaAs irradiated by high energy protons. Semiconductor Science and Technology, 1992, 7, 1237-1240.	1.0	22
4	Metastable population of self-organized InAs/GaAs quantum dots. Journal of Electronic Materials, 1999, 28, 491-495.	1.0	21
5	Thermal annealing of defects in InGaAs/GaAs heterostructures with three-dimensional islands. Semiconductors, 2000, 34, 195-204.	0.2	20
6	Hole and electron traps in the InGaAs/GaAs heterostructures with quantum dots. Physica B: Condensed Matter, 1999, 273-274, 959-962.	1.3	19
7	Tunnel coupling in an ensemble of vertically aligned quantum dots at room temperature. Physical Review B, 2009, 80, .	1.1	19
8	Capacitance spectroscopy of deep states in InAs/GaAs quantum dot heterostructures. Semiconductors, 1999, 33, 157-164.	0.2	16
9	Absorption in laser structures with coupled and uncoupled quantum dots in an electric field at room temperature. Semiconductors, 2009, 43, 490-494.	0.2	10
10	Optical properties of quantum-confined heterostructures based on GaP x N y As1 â˜' x â˜' y alloys. Semiconductors, 2011, 45, 1164-1168.	0.2	10
11	Stark effect in single and vertically coupled InAs/GaAs self-assembled quantum dots. Physica B: Condensed Matter, 2003, 340-342, 1103-1107.	1.3	9
12	Multiperiod quantum-cascade nanoheterostructures: Epitaxy and diagnostics. Semiconductors, 2014, 48, 1600-1604.	0.2	9
13	Study of deep levels in GaAs pâ€"iâ€"n structures. Semiconductors, 2016, 50, 924-928.	0.2	9
14	High-temperature diode formed by epitaxial GaP layers. Technical Physics Letters, 1998, 24, 329-331.	0.2	8
15	Wannier-Stark states in a superlattice of InAs/GaAs quantum dots. Semiconductors, 2010, 44, 761-765.	0.2	8
16	Ultra-wide electroluminescence spectrum of LED heterostructures based on GaPAsN semiconductor alloys. Semiconductors, 2014, 48, 501-504.	0.2	8
17	Misfit dislocationâ€"related deep levels in InGaAs/GaAs and GaAsSb/GaAs pâ€"iâ€"n heterostructures and the effect of these on the relaxation time of nonequilibrium carriers. Journal of Applied Physics, 2018, 123, 161588.	1.1	7
18	Spatial and Quantum Confinement of Si Nanoparticles Deposited by Laser Electrodispersion onto Crystalline Si. Technical Physics Letters, 2018, 44, 287-290.	0.2	7

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19	Localization of Holes in an InAsâˆ•GaAs Quantum-Dot Molecule. Semiconductors, 2005, 39, 119.	0.2	6
20	Coupling of electron states in the InAs/GaAs quantum dot molecule. Semiconductors, 2006, 40, 331-337.	0.2	6
21	Localized states in the active region of blue LEDs related to a system of extended defects. Technical Physics Letters, 2007, 33, 143-146.	0.2	6
22	Effect of Dislocation-related Deep Levels in Heteroepitaxial InGaAs/GaAs and GaAsSb/GaAs pâ€"iâ€"n Structures on the Relaxation time of Nonequilibrium Carriers. Semiconductors, 2018, 52, 165-171.	0.2	6
23	Metastable defects in as-grown and electron-irradiated. Semiconductor Science and Technology, 1996, 11, 1692-1695.	1.0	5
24	DLTS study of the Wannierâ€"Stark effect in Ge/Si QD superlattices. Physica B: Condensed Matter, 2007, 401-402, 576-579.	1.3	5
25	Room-temperature optical absorption in the InAs/GaAs quantum-dot superlattice under an electric field. Semiconductors, 2011, 45, 1064-1069.	0.2	5
26	Capacitance spectroscopy of structures with Si nanoparticles deposited onto crystalline silicon p-Si. Semiconductor Science and Technology, 2019, 34, 085003.	1.0	5
27	Stark effect in vertically coupled quantum dots in InAs-GaAs heterostructures. Semiconductors, 2002, 36, 1013-1019.	0.2	4
28	Polarization dependence of the stark shift in the absorption edge of InGaAs/GaAs quantum dot heterostructures. Technical Physics Letters, 2007, 33, 686-688.	0.2	4
29	Polarization dependences of electroluminescence and absorption of vertically correlated InAs/GaAs QDs. Semiconductors, 2012, 46, 93-98.	0.2	4
30	Deep-level defects in high-voltage AlGaAs pâ€"iâ€"n diodes and the effect of these defects on the temperature dependence of the minority carrier lifetime. Journal of Applied Physics, 2020, 128, 095705.	1.1	4
31	Effect of In and Al Content on Characteristics of Intrinsic Defects in GaAs-Based Quantum Dots. Semiconductors, 2004, 38, 209.	0.2	3
32	Wannier-stark effect in Ge/Si quantum dot superlattices. Semiconductors, 2008, 42, 305-309.	0.2	3
33	OPTICALLY-DETECTED MICROWAVE RESONANCE IN InGaAsN/GaAs QUANTUM WELLS AND InAs/GaAs QUANTUM DOTS EMITTING AROUND 1.3 Î¼m. International Journal of Nanoscience, 2003, 02, 469-478.	0.4	2
34	The Stark Shift of the Hole States in Separate InAsâˆ•GaAs Quantum Dots Grown on (100) and (311)A GaAs Substrates. Semiconductors, 2005, 39, 1053.	0.2	2
35	Coupling of quantum states in InAs/GaAs quantum dot molecule. AIP Conference Proceedings, 2007, , .	0.3	2
36	Stark effect in a multilayer system of coupled InAs/GaAs quantum dots. Technical Physics Letters, 2007, 33, 527-529.	0.2	2

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37	Deep-level transient spectroscopy studies of light-emitting diodes based on multiple-quantum-well InGaN/GaN structure. Physica B: Condensed Matter, 2009, 404, 4907-4910.	1.3	2
38	Passive mode-locked laser based on quantum dot superlattice. Technical Physics Letters, 2011, 37, 857-859.	0.2	2
39	Room temperature passive mode-locked laser based on InAs/GaAs quantum-dot superlattice. Nanoscale Research Letters, 2012, 7, 545.	3.1	2
40	Photoinduced conductivity and damage threshold of copper organoacetylenides illuminated with neodymium laser radiation. Soviet Journal of Quantum Electronics, 1976, 6, 151-153.	0.1	1
41	The influence of lattice mismatch upon defects generation and luminescent characteristics of heterostructures in the GaPâ€InP system. Crystal Research and Technology: Journal of Experimental and Industrial Crystallography, 1981, 16, 169-174.	0.3	1
42	pâ€“n and pâ€“nâ€“p junction arrays in CuInSe2 crystals: Cathodoluminescence and capacitance study. Journal of Applied Physics, 1997, 82, 5167-5175.	1.1	1
43	Cathodoluminescence of p-n-p microstructures in CuInSe2 crystals. Semiconductors, 1997, 31, 92-96.	0.2	1
44	The influence of Coulomb effects on the electron emission and capture in InGaAs/GaAs self-assembled quantum dots. Physica B: Condensed Matter, 2001, 308-310, 1113-1116.	1.3	1
45	Deep levels in the band gap of GaN layers irradiated with protons. Semiconductors, 2002, 36, 1352-1354.	0.2	1
46	Effect of Coulomb charge on properties of arsenic vacancy in GaAs-based quantum dots. Physica B: Condensed Matter, 2003, 340-342, 1133-1136.	1.3	1
47	Wannier-Stark Effect in InAsâˆ•GaAs Quantum-Dot Superlattice. AIP Conference Proceedings, 2011, , .	0.3	1
48	Polarization dependences of electroluminescence and absorption of vertically correlated InAs/GaAs QDs. , 2013, , .		1
49	Deep-level transient spectroscopy of InAs/GaAs quantum dot superlattices. , 2014, , .		1
50	Influence of GaAs spacer-layer thickness on quantum coupling and optical polarization in a ten-layer system of vertically correlated InAs/GaAs quantum dots. Semiconductors, 2014, 48, 1031-1035.	0.2	1
51	Impact of the Percolation Effect on the Temperature Dependences of the Capacitanceâ€“Voltage Characteristics of Heterostructures Based on Composite Layers of Silicon and Gold Nanoparticles. Semiconductors, 2019, 53, 1393-1397.	0.2	1
52	Capacitance Spectroscopy of Heteroepitaxial AlGaAs/GaAs pâ€“iâ€“n Structures. Semiconductors, 2020, 54, 1260-1266.	0.2	1
53	Deep level defects in GaAs gradual p-i-n junctions after neutron irradiation. Journal of Physics: Conference Series, 2022, 2227, 012019.	0.3	1
54	Effect of Neutron Irradiation on the Spectrum of Deep-Level Defects in GaAs Grown by Liquid-Phase Epitaxy in a Hydrogen and Argon Atmosphere. Semiconductors, 0, , .	0.2	1

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55	The study of the influence of deep level defects on GaAs epilayer electrophysical parameters with electron beam and photoelectron paramagnetic resonance methods. Crystal Research and Technology, 1985, 20, 1387-1391.	0.6	0
56	Study of electron capture by quantum dots using deep-level transient spectroscopy. Semiconductors, 2001, 35, 1175-1181.	0.2	0
57	Emission spectra of a laser based on an In(Ga)As/GaAs quantum-dot superlattice. Semiconductors, 2015, 49, 1335-1340.	0.2	0
58	10.1007/s11453-008-3011-8. , 2010, 42, 305.		0